## 2SD1269

## Silicon NPN epitaxial planar type

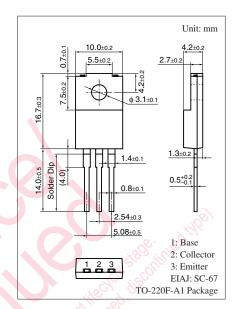
For power switching Complementary to 2SB0944

#### ■ Features

- Low collector-emitter saturation voltage V<sub>CE(sat)</sub>
- $\bullet$  Satisfactory linearity of forward current transfer ratio  $h_{\text{FE}}$
- Large collector current I<sub>C</sub>
- Full-pack package which can be installed to the heat sink with one screw.

### ■ Absolute Maximum Ratings $T_C = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	130	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	80	V	
Emitter-base voltage (Collector open)	$V_{EBO}$	7	V	
Collector current	$I_C$	4	A	
Peak collector current	I <sub>CP</sub>	8	A	
Collector power	P <sub>C</sub>	35	W	
dissipation $T_a = 25^{\circ}C$		2.0		
Junction temperature	$T_{j}$	150	°C	
Storage temperature	$T_{stg}$	-55 to +150	°C	



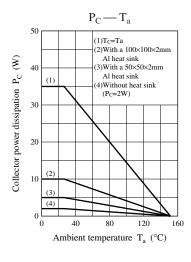
### ■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

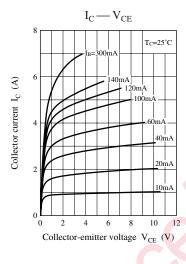
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 10 \text{ mA}, I_B = 0$	80			V
Collector-base cut-off current (Emitter open)	$I_{CBO}$	$V_{CB} = 100 \text{ V}, I_E = 0$			10	μΑ
Emitter-base cut-off current (Collector open)	I <sub>EBO</sub>	$V_{EB} = 5 \text{ V}, I_C = 0$			50	μΑ
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = 2 \text{ V}, I_{C} = 0.1 \text{ A}$	45			_
	h <sub>FE2</sub> *	$V_{CE} = 2 \text{ V}, I_{C} = 1 \text{ A}$	60		260	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 3 \text{ A}, I_B = 0.15 \text{ A}$			0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 3 \text{ A}, I_B = 0.15 \text{ A}$			1.5	V
Transition frequency	$f_T$	$V_{CE} = 10 \text{ V}, I_{C} = 0.5 \text{ A}, f = 10 \text{ MHz}$		30		MHz
Turn-on time	t <sub>on</sub>	$I_C = 1 A$ , $I_{B1} = 0.1 A$ , $I_{B2} = -0.1 A$		0.5		μs
Storage time	t <sub>stg</sub>	$V_{CC} = 50 \text{ V}$		2.5		μs
Fall time	$t_{\rm f}$			0.15		μs

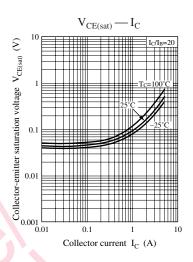
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

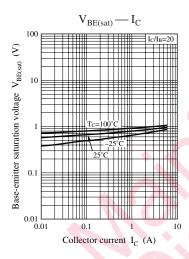
#### 2. \*: Rank classification

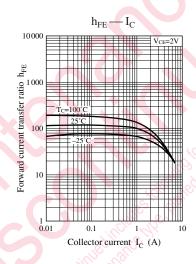
Rank	R	Q	Р
h <sub>FE2</sub>	60 to 120	90 to 180	130 to 260

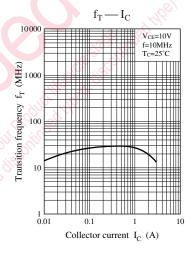


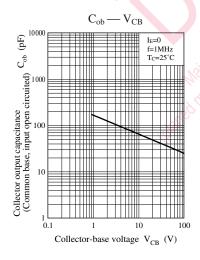


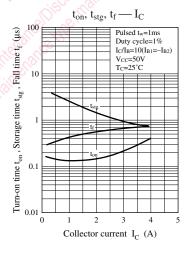


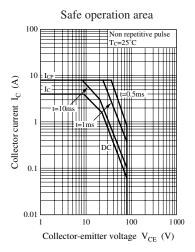


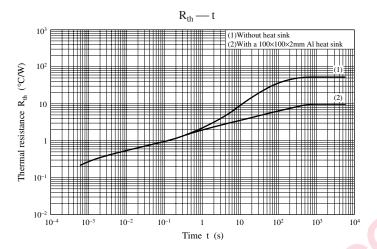












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